



AN 344

Micro-Analytical Evaluation of Via Etch Processes and Post-Etch Cleaning Procedures

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Discussion

The micro-analytical evaluation of via sidewall contamination and the chemical characterization of residues inside of vias is of critical importance for the evaluation of via etch processes and post-etch cleaning procedures. With critical dimensions shrinking typical via diameters are now at and below 0.25 μm . Etch residues may be in the order of 100 nm in size or less. The spatial resolution and sensitivity required for an analysis of such residues poses a major challenge for advancements outlined in the semiconductor roadmap.

Traditional EDS (Energy Dispersive X-ray Spectroscopy) typically lacks surface sensitivity to analyze sidewall deposits that are in the order of a few atomic layers thick or less. Even for residues with nanometer thickness a high level of ambiguity exists on whether a signal arises from the actual residue or whether it is from layers underneath the residue. FE-AES (Field Emission-Auger Electron Spectroscopy) has a sampling depth of only ~ 20 to 40 \AA providing a tremendous advantage over EDS for the analysis of sidewall contamination and via residues.

In the example presented a copper layer at the bottom of a via was opened by etching through a silicon carbide layer that was on top of the copper. An AES copper linescan along a via cross section showed that copper is present on the via sidewall and (preferentially) accumulated towards the via opening (Figures 1 and 2). An AES copper map acquired from the top surface also indicates that Cu accumulated at the via opening (Figure 3).

AES is uniquely suited for via analyses in that it is fast, inexpensive and reliable. Alternative methods include electrical testing and TEM/EELS. Electrical testing requires fabrication of a test structure which is time consuming and expensive. In addition data interpretation is highly ambiguous. TEM/EELS lacks sensitivity for monolayer contamination levels.

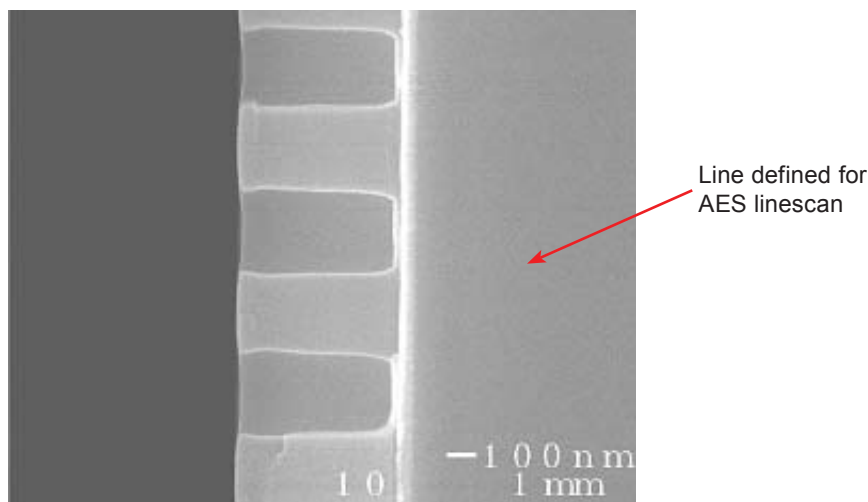


Figure 1. SEM image of via cross section

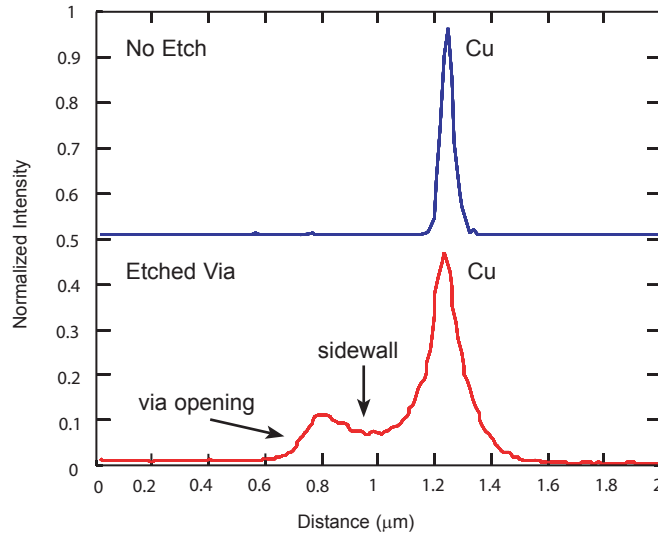


Figure 2. Cu linescans along via cross sections

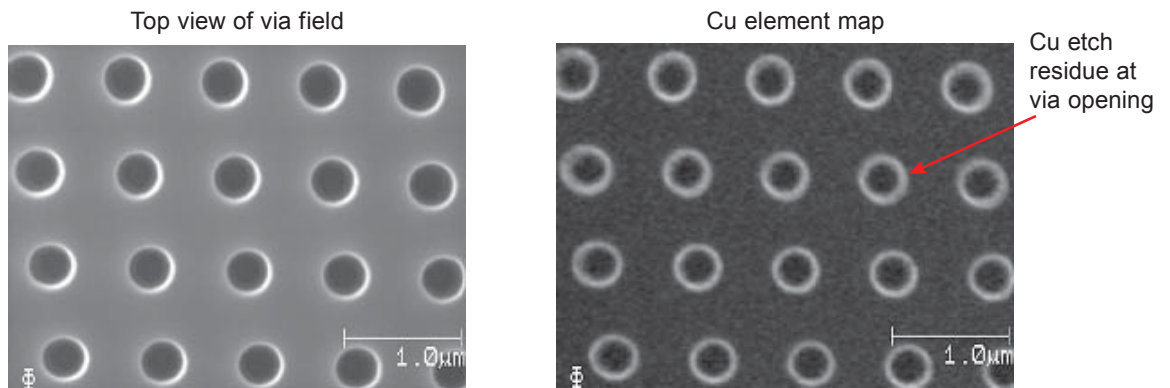


Figure 3

United States Locations

Tempe, Arizona
 +1 480 239 0602 info.az@eaglabs.com
 +1 602 470 2655 fax

Sunnyvale, California
 810 Kifer Road
 +1 408 530 3500 info.ca@eaglabs.com
 +1 408 530 3501 fax

1135 E Arques Avenue
 +1 408 738 3033
 +1 408 738 3035 fax

785 Lucerne Drive
 +1 408 737 3892
 +1 408 737 3916 fax

Peabody, Massachusetts
 +1 978 278 9500 info.ma@eaglabs.com
 +1 978 278 9501 fax

Chanhassen, Minnesota
 +1 952 828 6411 info.mn@eaglabs.com
 +1 952 828 6449 fax

East Windsor, New Jersey
 +1 609 371 4800 info.nj@eaglabs.com
 +1 609 371 5666 fax

Syracuse, New York
 +1 315 431 9900 info.ny@eaglabs.com
 +1 315 431 9800 fax

Raleigh, North Carolina
 +1 919 829 7041 info.nc@eaglabs.com
 +1 919 829 5518 fax

Round Rock, Texas
 +1 512 671 9500 info.tx@eaglabs.com
 +1 512 671 9501 fax

International Locations

Shanghai, China
 + 86 21 6879 6088 info.cn@eaglabs.com
 + 86 21 6879 9086 fax

Tournefeuille, France
 + 33 5 61 73 15 29 info.fr@eaglabs.com
 + 33 5 61 73 15 67 fax

Frankfurt, Germany
 + 49 (0) 693053213 info.de@eaglabs.com
 + 49 (0) 69307941 fax

Tokyo, Japan
 + 81 3 5396 0531 info.jp@eaglabs.com
 + 81 3 5396 1930 fax

HsinChu, Taiwan
 + 886 3 5632303 info.tw@eaglabs.com
 + 886 3 5632306 fax

Uxbridge, United Kingdom
 + 44 (0) 1895 811194 info.uk@eaglabs.com
 + 44 (0) 1895 810350 fax